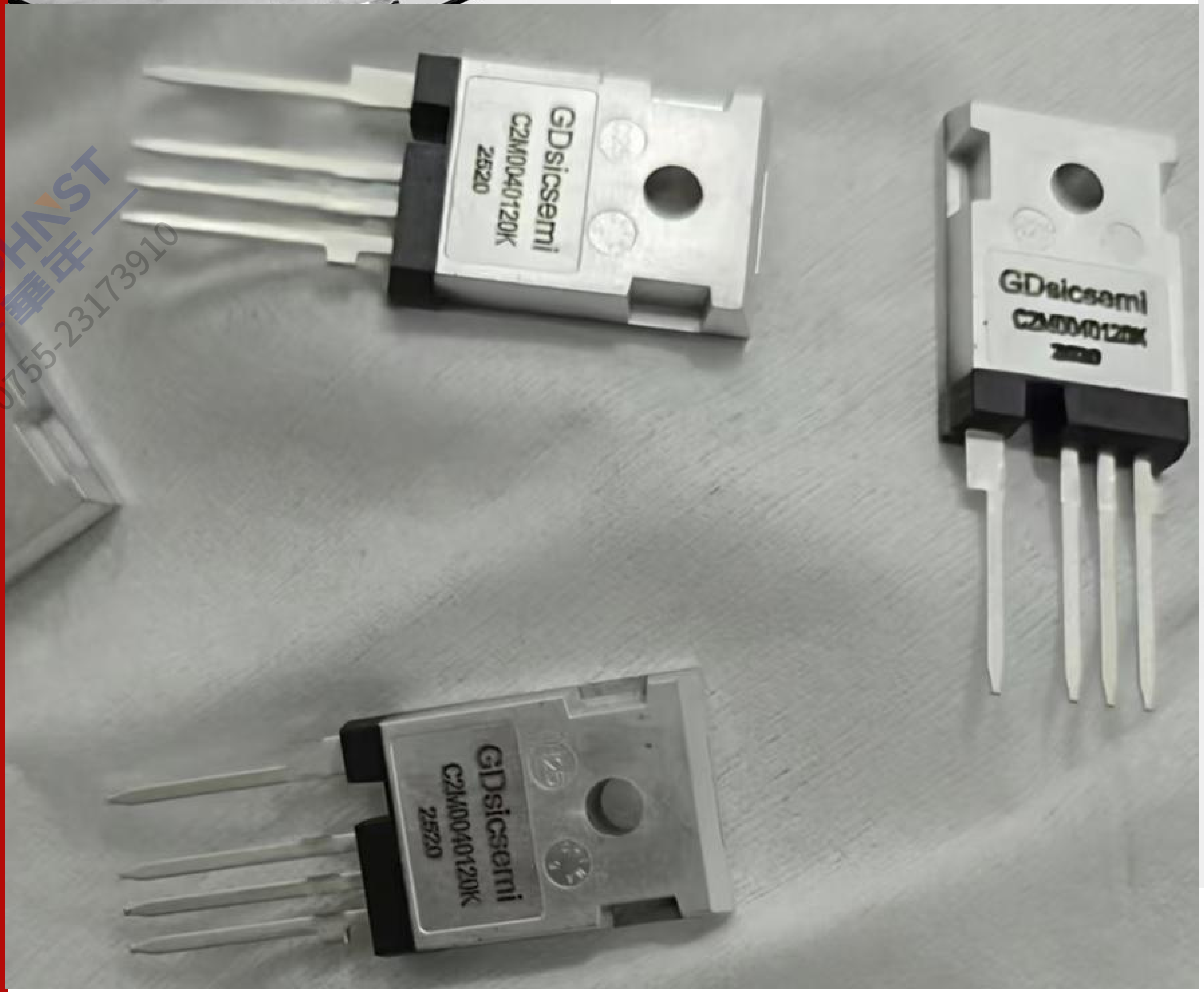
GDsicsemi

Innovator of

Nano Meter Coating (NMC) Techniques

GD SiC Semi Co.

COMPANY PROFILE



~a Great Deal for the Future!

惠州市广大碳基半导体有限公司

Business Scope

GDsicsemi

01

SiC Chip Design Foundry Services

02

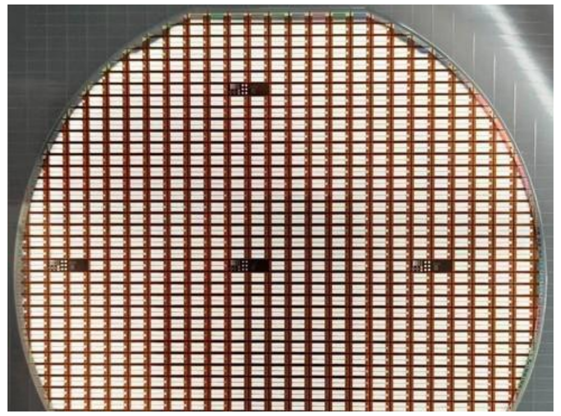
SiC Chip Assembly/ Testing Services

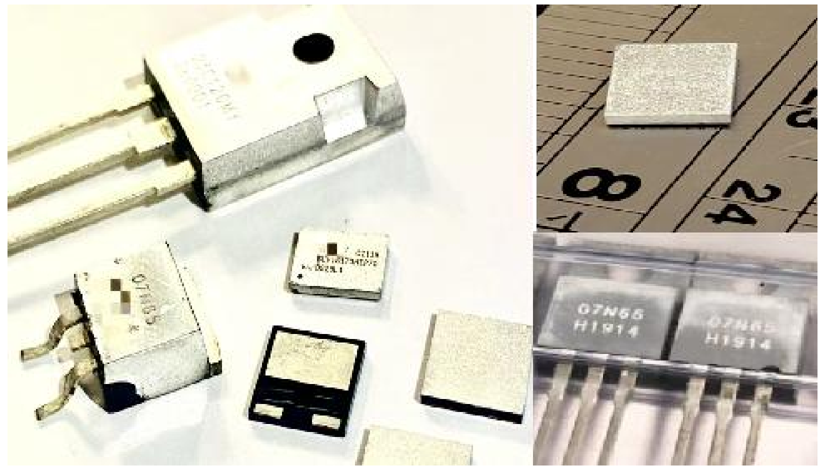
03

SiC Discrete & Module Solution

04

Nano Meter Coating Services





Company Qualifications

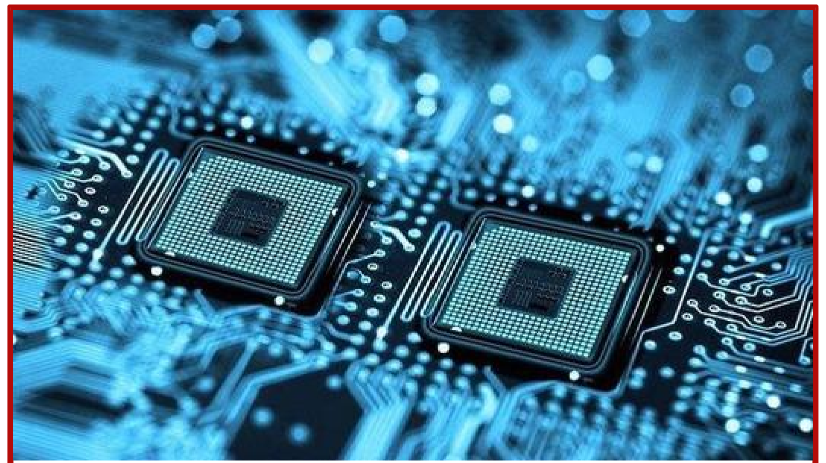
GDsicsemi

IATF16949

Obtained the IATF16949 quality management system standard certification

Obtained the ISO9001:2015 quality management system standard certification

The component has passed 100 hours of reliability certification



The product is doing AEC-Q101 certification and is expected to pass in March 2024

Certificates

GDsicsemi

qualityaustria
Succeed with Quality

IATF

CERTIFICATE
质量管理体系认证证书

Quality Austria - Trainings, Zertifizierungs und Begutachtungs GmbH 颁发证书给下列机构：

惠州市广大碳基半导体有限公司
中国广东省惠州市仲恺高新区潼侨镇联发大道南面
华创伟工业园厂房第 4 栋 1 楼 A 区

碳化硅半导体电子元器件的生产

兹证明：

质量管理体系
符合下列标准要求
IATF 16949:2016
不含产品设计

注册编号：T-13987/0
IATF-USI:Y9SC62
IATF 注册号：0490199
发证日期：2023 年 11 月 30 日
有效期限：2026 年 11 月 29 日

维也纳, 2023 年 11 月 30 日 Page 1 / 1

Quality Austria - Trainings, Zertifizierungs und Begutachtungs GmbH,
AT-1010 Vienna, Zelinkagasse 10/3

Mag. Christoph Mondl
CEO

Mag. Dr. Werner Paar
CEO

Ing. Michael Dragosits, MSc
Specialist representative

第一次监审合格标志 第二次监审合格标志

Dok.Nr.FO_24_029

Quality Austria 奥世认证标志确认记录

获证企业统一社会信用代码/组织机构代码：91441303MA7LUXP87B
本证书信息可在国家认证认可监督管理委员会官方网站（www.cnca.gov.cn）上查询

IATF 16949:2016

Certificates

GDsicsemi

qualityaustria
Succeed with Quality

CERTIFICATE
质量管理体系认证证书

Quality Austria - Trainings, Zertifizierungs und Begutachtungs GmbH 颁发证书给下列机构：

惠州市广大碳基半导体有限公司
注册地址：惠州市仲恺高新区潼侨镇联发大道南面华创伟工业园厂房第 4 栋 1 楼 A 区
认证地址：中国广东省惠州市仲恺高新区潼侨镇联发大道南面华创伟工业园厂房第 4 栋 1 楼 A 区

碳化硅半导体电子元器件的生产

获证机构将通过每年的监督审核，取得“qualityaustria 奥世认证确认证书”方可维持该证书的有效性；每三年将进行一次重新审核。

兹证明：

质量管理体系
符合下列标准要求
ISO 9001:2015

注册编号：28463/0
初次发证日期：2022 年 11 月 16 日
有效期限：2025 年 11 月 15 日

维也纳, 2022 年 11 月 16 日

IAF
qualityaustria
IQNET

Quality Austria - Trainings, Zertifizierungs und Begutachtungs GmbH, AT-1010 Vienna, Zelinkagasse 10/3

Mag. Christoph Mondl
CEO

Mag. Dr. Werner Paar
CEO

Mag. Dr. Anni Koubek
Specialist representative

Quality Austria - Trainings, Zertifizierungs und Begutachtungs GmbH is accredited according to the Austrian Accreditation Act by the BMWFW (Federal Ministry of Science, Research and Economy).

Quality Austria is accredited as an organisation for environmental verification by the BMLFUW (Federal Ministry of Agriculture, Forestry, Environment and Water Management).

Quality Austria is authorized by the VDA (Association of the Automotive Industry).

For accreditation registration details please refer to the applicable decisions or recognition documents.

Quality Austria is the Austrian member of IQNet (International Certification Network).

The current validity of the certificate is documented exclusively on the Internet under http://www.qualityaustria.com/en/cert

获证企业统一社会信用代码/组织机构代码:91441303MA7LUXP87B
本证书信息可在国家认证认可监督管理委员会官方网站（www.cnca.gov.cn）上查询

ISO 9001:2015

GDsicsemi

Production capacity

Package	Capacity
TO247-4	1.5KK
TO247-3	1KK
TO247-2	1KK
TO220-2	2KK
SOP-4	3KK
DIP-4	2KK
DIP-8	2KK
TO3PF	2KK

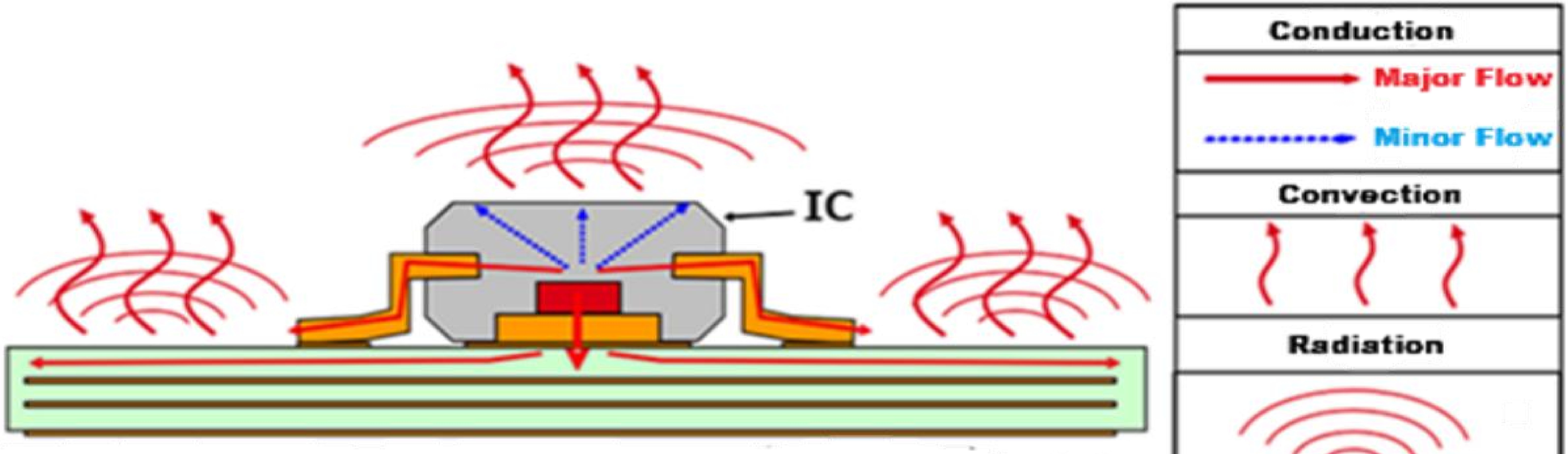
Nano Meter Coating Introduction

1. Theory

2. Examples

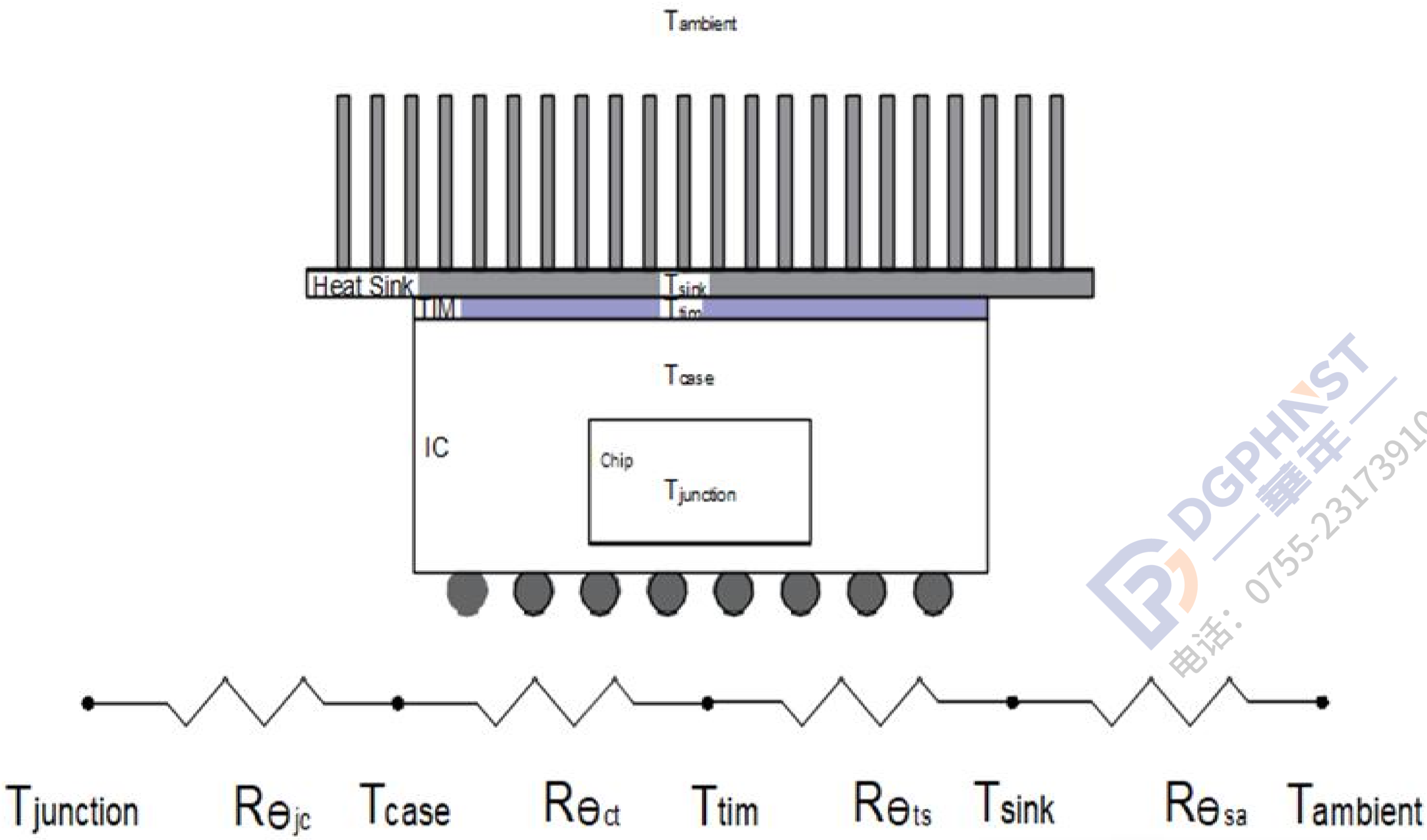
3. Applicable Criteria

GDsicsemi



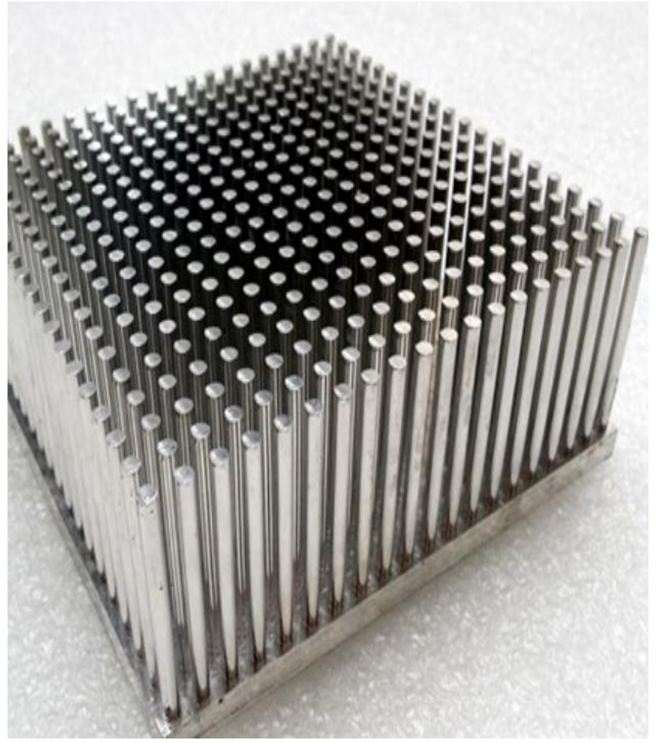
Heat Dissipation flows of Lead Type Devices on FR4 in sectional view

GDsicsemi

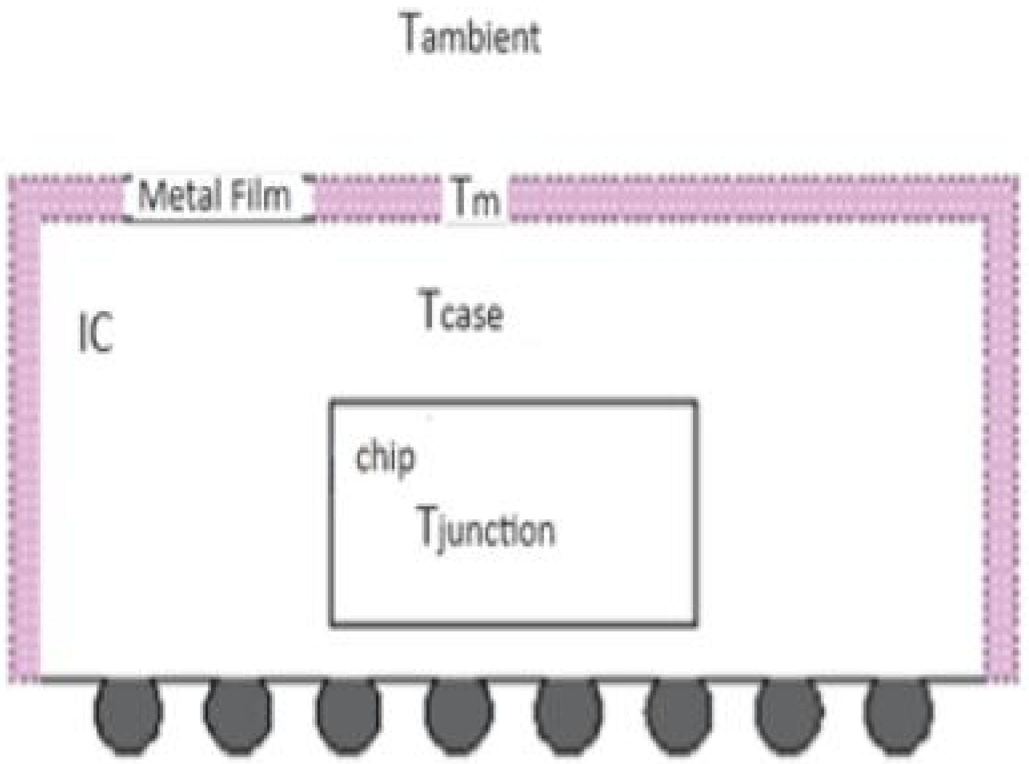


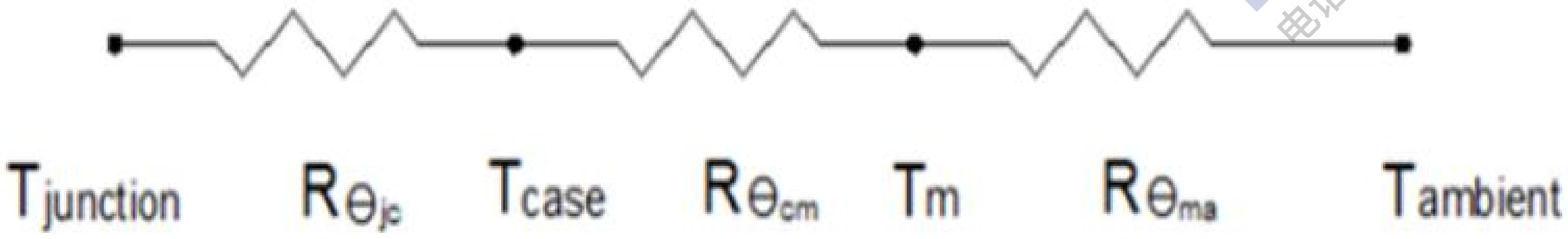
Current solution and hotspots

Traditional method is to use TIM(adhesive) to conduct Heat Sink with huge size and complex procedures to bring heat from chip junction to surface in order to gain heat convection and radiation Effects with extra ventilation with air- cooled or even liquid cooled solution. A migration improved techniques or materials from Nickel films and Graphite layers are all with similar purposes to help sinking heat. But truth is, with TIM(or adhesive) To attach either either metal or graphite would hugely lower down heat conduction, in addition, the Thermal Conductivity and Diffusivity of different material i.e. Nickel and Graphite are relatively much lower with another difficulty to be formed in < 5um that also prominently decrease heat dissipation both on devices and systems… Furthermore, complex manufacturing accomplished with longer production time and low UPH with higher costs generated.



GDsicsemi





Now, the revolutionary Nano Meter Coating (NMC) on Chips debuts

With NMC on chips, metal coated on 1 or even 5 surfaces on Any package types of ICs and discrete devices can effectively and efficiently conduct, convect and radiate heat generated inside molding compound to open air with ventilation or even liquid- cooled solution. Comparing with traditional heatsink with adhesive or TIM, only < 200nm metal film is Coated on products with low costs and high productivity to remain almost similar heat dissipation performance without huge size in occupied system. Also, better Anti- EMI ability can be anticipated.

Experiment # 1: M.2 SSD Module Comparison

GDsicsemi

Controller (Marvell_SS1331_356- Ball FC_BGA) Average Temp. Comparison

Ambient Temp (°C)	W/ NMC Avg. Temp (°C)	Non- NMC Avg. Temp(°C)	Avg. Δ T (°C) After NMC
0	35.55	46.83	-11.28
25	71.15	78.70	-7.55
70	96.73	102.55	-5.82

Controller (Marvell_SS1331_356- Ball FC_BGA) Peak Temp. Comparison

Ambient Temp (°C)	W/ NMC Peak Temp (°C)	Non- NMC Peak Temp(°C)	Δ T (°C) After NMC
0	73.00	82.50	-9.50
25	111.50	128.00	-16.50
70	119.50	138.50	-19.00

FLASH Memory (512GB 291- Ball FC_BGA) Average Temp. Comparison

Ambient Temp (°C)	W/ NMC Avg. Temp (°C)	Non- NMC Avg. Temp(°C)	Avg. Δ T (°C) After NMC
0	32.80	36.95	-4.15
25	59.20	64.45	-5.25
70	84.63	89.95	-5.32

Experiment #2: Cool MOS & SiC MOSFET w/ or w/ o active Ventilation

GDsicsemi

PPAK5*6 Cool MOS Coating V.S. Non Coating

Condition	Method	Body Diode	IF	VF	Power	T1	T2	Delta T	ΔT
w/o Ventilation	IR Thermometer	Non Coating	1.799	0.554	0.997	24	85.8	61.8	-15.8
		Coating	1.799	0.555	0.998	24	70	46	
	Thermocouple	Non Coating	1.8	0.554	0.997	24	68	44	-10.1
		Coating	1.8	0.55	0.99	24	57.9	33.9	
With Ventilation	IR Thermometer	Non Coating	1.8	0.59	1.062	24	66.2	42.2	-21.6
		Coating	1.8	0.594	1.069	24	44.6	20.6	
	Thermocouple	Non Coating	1.8	0.59	1.062	24	47.8	23.8	-14.1
		Coating	1.8	0.595	1.071	24	33.7	9.7	

TO-247 SiC MOSFET Coating V.S. Non Coating

Condition	Method	Body Diode	IF	VF	Power	T1	T2	Delta T	ΔT
w/o Ventilation	IR Thermometer	Non Coating	1.5	2.183	3.275	24	105	81	-69.1
		Coating	1.5	2.115	3.173	24	35.9	11.9	
	Thermocouple	Non Coating	1.5	2.182	3.273	24	95.2	71.2	-10.3
		Coating	1.5	2.115	3.173	24	84.9	60.9	
With Ventilation	IR Thermometer	Non Coating	1.5	2.286	3.429	24	74	50	-43.1
		Coating	1.5	2.142	3.213	24	30.9	6.9	
	Thermocouple	Non Coating	1.5	2.284	3.426	24	64.9	40.9	-15.2
		Coating	1.5	2.178	3.267	24	49.7	25.7	

Note: T1= Ambient Temp.

GDsicsemi

Experiment # 3: DDR5 mini DIMM with i7 13xx Series @ 7800 MT/ s

Non- NMC Items

Unit: ℃

Dimm #2, Air- cooled	IC # 2	IC # 7	PMIC	SPD Hub Readings	Room Temp
Stand- by Temp.	21.9	22.1	22.3	22	21.3
3 Min. Burn- in	46.2	47.1	39.9	53	
5 Min. Burn- in	52.8	51.3	40.6	55	
Peak Temp.	53.3	49.6	41.2	56	
Off after 1 Min.	38	39.4	36.1	41	
Off after 3 Min.	27	28.7	28.6	31	

NMC Items

Dimm #2, Air- cooled	IC # 2	IC # 7	PMIC	SPD Hub Readings	Room Temp
Stand- by Temp.	22.1	23.6	21.7	23	21.6
3 Min. Burn- in	40.0	39.9	33.2	41	
5 Min. Burn- in	40.1	40.0	33.1	40	
Peak Temp.	41.6	41.2	33.6	41	
Off after 1 Min.	32.9	33.5	29.5	33	
Off after 3 Min.	22.0	22.5	22.3	23	

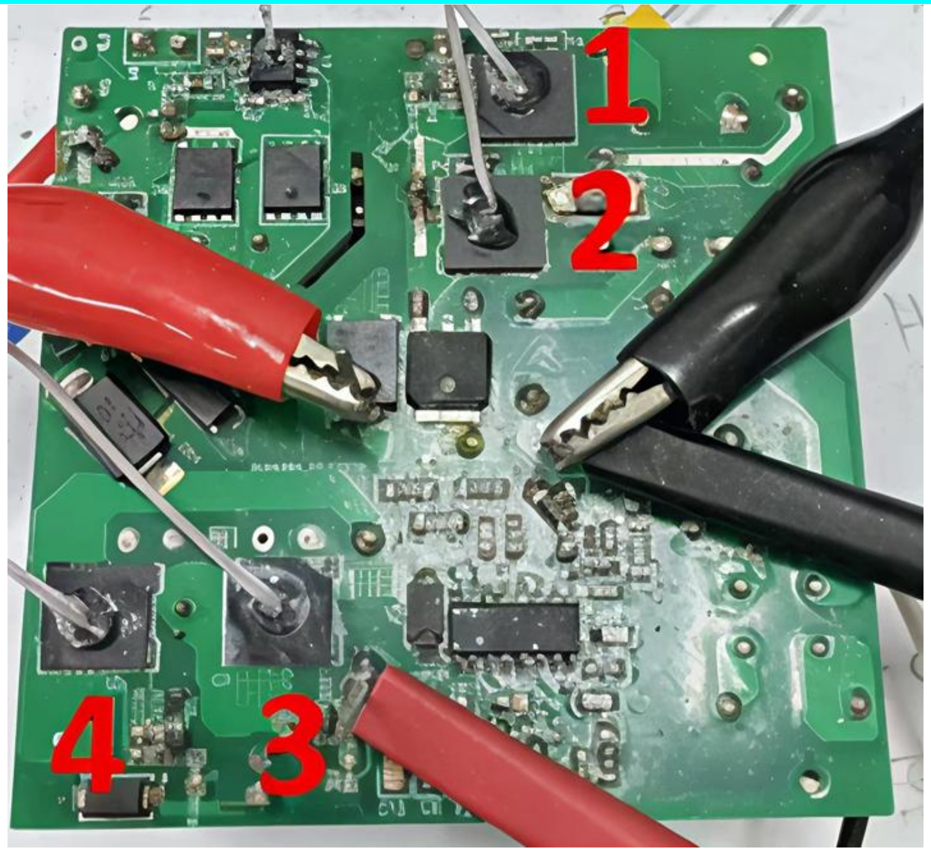
In comparing Burn- in test of DDR5 accompanied with INTEL CPU i7 Gen 13, Running R/W frequency @ 7800 MT/ S. Ventilation with Air- cooling fan. Per experience, the system reaches heat balance state after 5 min. We noticed some clues that DIMM with NMC preforms

1. Shorter time to achieve heat balance with red circles within maybe 3 mins. and
2. 11 ℃ cooler on DDR Chips, and 6 ℃ on PMICs
3. Quicker heat dissipation after system being turned- off

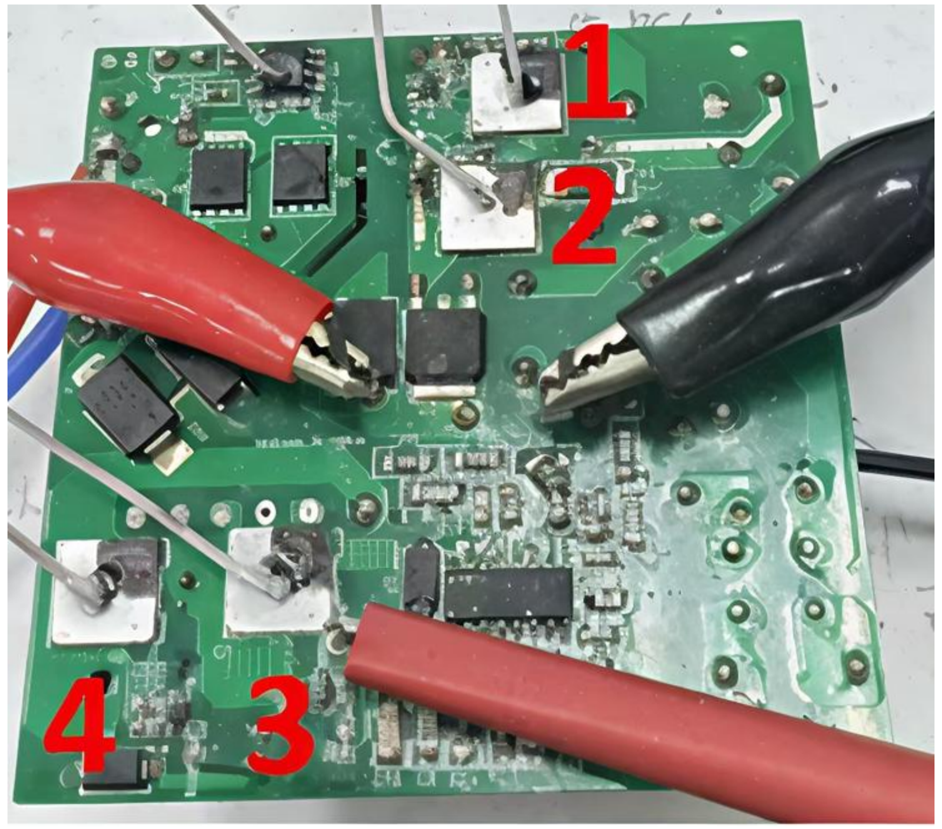
To conclude, NMC might help enhancing AC parameters on DDR Chips and system stability affiliated to cooler PMICs. Also, Overclocking with CPU might be much easier and sustain longer when boosting.

Experiment # 4: DFN Gan HEMT in open frame thermal impedance test

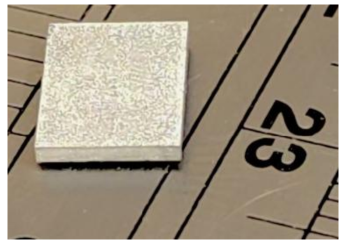
NON-NMC
Vin: 115 VAC
Output: 5A/ 20V



After NMC
Vin: 115VAC
Output: 5A/ 20V



Gan HEMT P/N: MGZ18N65, 130mΩ/ 650V



100W Full Load Burn- in for **1 Min.** **Unit: ℃**

	w/o NMC	with NMC	Δ T
CH1	61.7	66.4	4.7
CH2	65.1	69.2	4.1
CH3	53.6	57.0	3.4
CH4	52.4	56.2	3.8

100W Full Load Burn- in for **5 Min.** **Unit: ℃**

	w/o NMC	with NMC	Δ T
CH1	78.8	69.4	-9.4
CH2	81.6	71.9	-9.7
CH3	71.7	62.6	-9.1
CH4	72.4	63.2	-9.2

Ta= 29.8 ℃

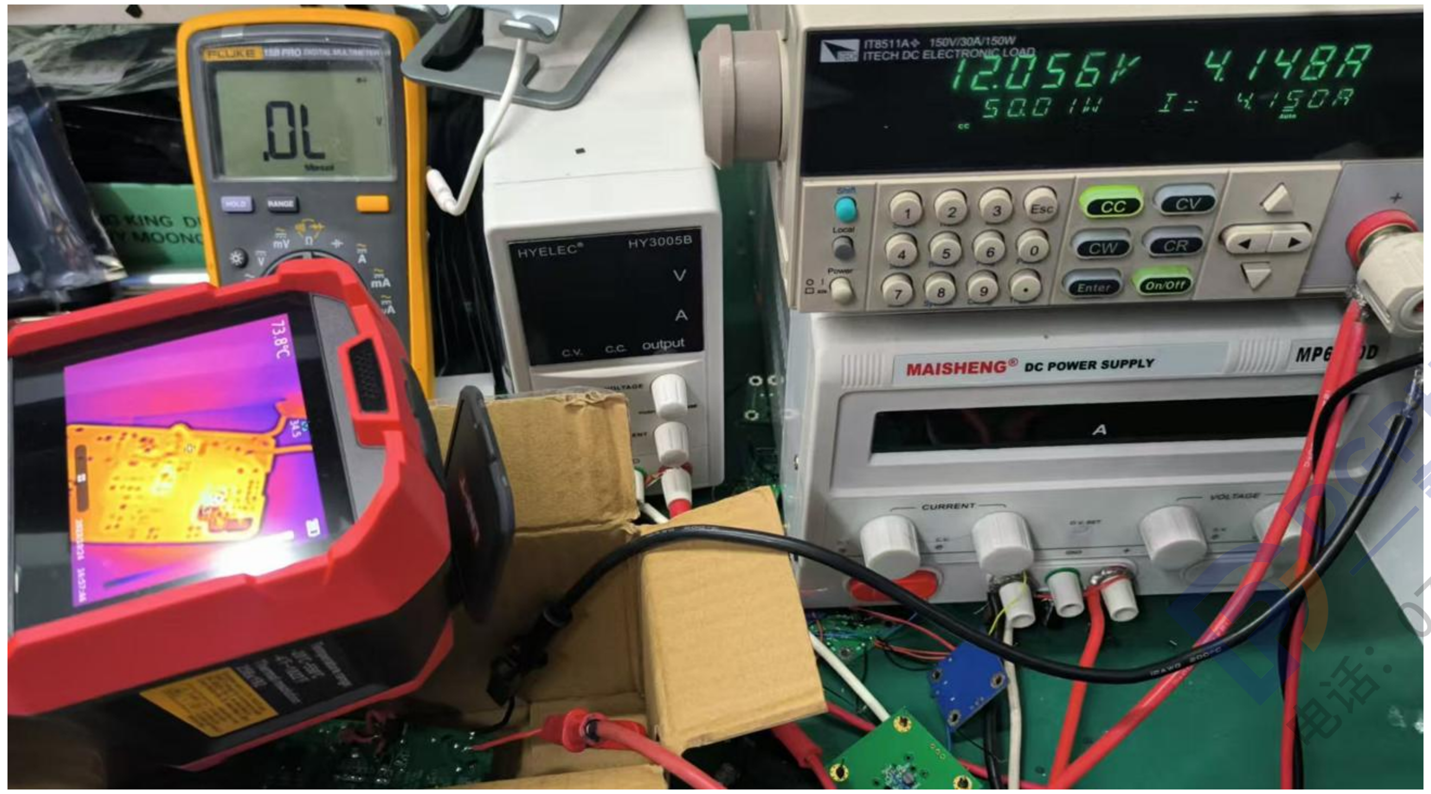
Due to thin DFN package and high duty cycle and operating frequency, at the very early stage **before thermal balance**, the heat generated by the rapid rising junction Temp. is conducted through molding compound with high thermal impedance to the surface with ultra- thin aluminum film (< 150nm), the thermal impedance **sharply** declines to almost **Zero,** GaN HEMT with NMC rapidly conducts and convets heat through metal films compared with non- Coating FETs, this reflects on around 4℃ higher surface Temp. in early stages.

After reaching **thermal balance** in open frame without active ventilation, NMC HEMTs are > 9 ℃ cooler than non NMC ones.

Experiment # 5: TO-252 SiC MOSFET on 50W Charger in enclosed space

GDsicsemi

NON-NMC
Vin: 225 Vac
Output: 4.15A/ 12V



50W Full Load Burn- in for **15 Min.**
@ > 70℃

Ta= 26.8 ℃

After NMC
Vin: 225 VAC
Output: 4.15A/ 12V

50W Full Load Burn- in for 15 **Min.**
@ < 45 ℃

SiC MOSFET P/N: SMC300N065DAS, 260mΩ/ 650V

In this significant experiment imitating confined switching adaptor/ charger with effective output of 50W(12V/ 4.15A) under restrained space of sample box, reaching out thouroughly thermal balance after 15 min. of burn- in, Engineer opened up sample box and immediately measured SiC MOSFETs w/ and W/O NMC to compare top side Temp. of each FET. We therefore conclude accordingly the prominent Temp. gap between FETs with and without NMC to be outrageously > 25 ℃ **with such a small output power device with no ventilation assisted.**

Another stunning rapid heat dissipation evidence coming from Zero Thermal Impedance of NMC is remarked that during the sudden exposure to open air, FETs with NMC performed sharply temp. decline comparing with non NMC FETs. The NMC FETs Temp. drop > 15 ℃ within 10 sec. when being encountered fresh air.

TCT Verification Report: Thermal Shock Resistance of NMC Nanocoating

INTEGRATED SERVICE TECHNOLOGY
Integrated Service Technology Inc.
Reliability & Failure Analysis Engineering Group
No.10-1, Lixing 1st Rd., East Dist., Hsinchu City 300, Taiwan (R.O.C.).
Tel: 886-3-579-9909, Fax: 886-3-563-4868
http://www.istgroup.com

2. TEMPERATURE CYCLING TEST

2.1 TEST EQUIPMENT

Test Equipment	Serial Number	Calibration Expiration
KSON TSC-E5T-150	A0886	AUG 19, 2025

2.2 LABORATORY AMBIENCE CONDITION

Temperature：25 °C ± 5 °C

Relative humidity：55 % ± 15 % (RH)

2.3 REFERENCE DOCUMENT

The test is based on customer specification. (as 2.4 test condition)

2.4 TEST CONDITION

Units are non-operating.

Temperature range：-40 °C to +85 °C

Dwell time：10 minutes

Ramp up time：40 minutes

Ramp down time：90 minutes

Cycle time：150 minutes

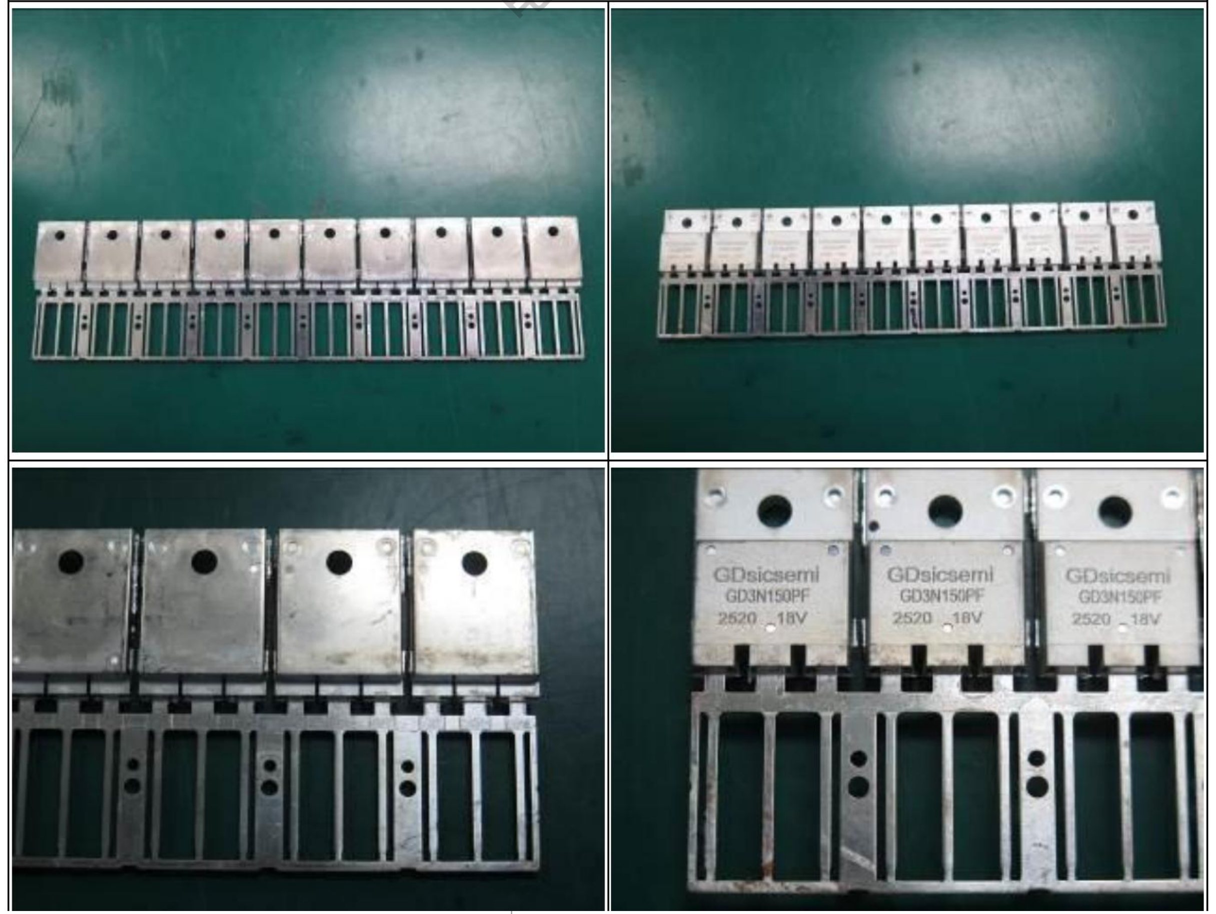
Number of cycles：200 cycles

2.5 SUMMARY OF TEST

Functional check is performed by customer without 3rd party lab (iST) person participated.

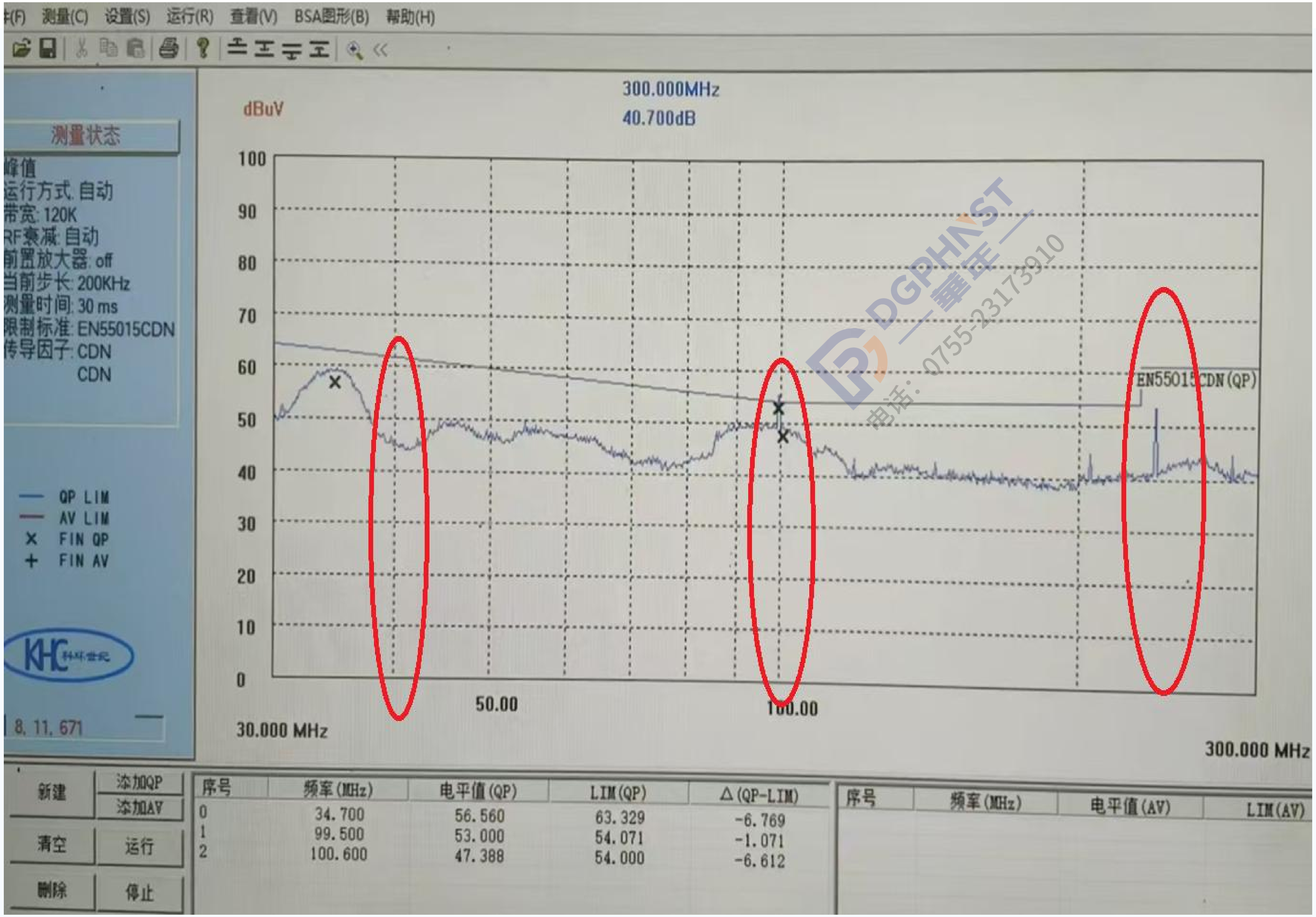
After testing, visual inspection of sample surfaces showed no abnormity.

After testing
T0-3PF
#1



After testing
T0-220F
#1

NMC Nanocoating Radiated Emissions (RE) Test Report



GDsicsemi

Customer tests confirm that devices coated with NMC film demonstrate exceptional EMI radiation suppression in the challenging 30MHz~100MHz frequency band, achieving compliance with substantial margin.

Conduction Advantages via Third-Generation Materials

In conducted EMI scenarios, leveraging the inherent physical advantages of third-generation semiconductor materials:

- **Zero parasitic oscillation**
- **Ultra-low output capacitance (Coss) and reverse transfer capacitance (Crss)**
- **Faster switching characteristics (high di/dt during turn-on, steep dv/dt during turn-off)**
- **Low gate charge (Qg)**
- **Absence of reverse recovery charge (Qrr)**

These properties significantly reduce the need for magnetic filtering components on the PCB, lowering both BOM costs and layout space requirements.

GDsicsemi

Product List

* **NMC SiC Schottky Barrier Dodes**
  NMC 碳化硅肖特基二极管

* **NMC SiC MOSFET**
  NMC碳化硅场效应**MOS**管

* **Nano Meter Coating Services**
  NMC纳米金属镀层服务

月量产产能

GDsicsemi

- TO247- 1.5KK
- TO247- 1.5KK
- TO247- 1.5KK
- TO220- 3KK

- SOP- 3KK EOL in Q3’25
- DIP- 2KK EOL in Q3’25
- DIP- 2KK EOL in Q3’25
- TO3PF 3KK

GDsicsemi

• SiC SBD – A

SiC Schottky diodes	Voltage	Current	VF	Packaging	
C3D10065A	650V	10A	1.4V	TO220-2	
C3D20065A	650V	20A	1.4V	TO220-2	
C3D20065D	650V	20A	1.4V	TO247-3	
C6D06120A	1200V	6A	1.27V	TO220-2	
C4D05120A	1200V	5A	1.4V	TO220-2	
C4D08120A	1200V	8A	1.4V	TO220-2	
C4D10120A	1200V	10A	1.35V	TO220-2	
C4D12120A	1200V	12A	1.35V	TO220-2	
C6D16120A	1200V	16A	1.27V	TO220-2	
C6D15120A	1200V	15A	1.27V	TO220-2	
C4D20120A	1200V	20A	1.4V	TO220-2	
C3D10170A	1700V	10A	1.7V	TO220-2	

SiC SBD - B

GDsicsemi

SiC Schottky diodes	Voltage	Current	VF	Packaging	
C3D30065D	650V	30A	1.4V	TO247-3	
C4D10120D	1200V	10A	1.4V	TO247-3	
C4D15120D	1200V	15A	1.4V	TO247-3	
C4D20120DSOI	1200V	20A	1.4V	TO247-3	Ceramic isolation
C4D20120D	1200V	20A	1.4V	TO247-3	
C4D30120DSOI	1200V	30A	1.4V	TO247-3	Ceramic isolation
C4D30120D	1200V	30A	1.4V	TO247-3	
C4D40120DSOI	1200V	40A	1.4V	TO247-3	Ceramic isolation
C4D40120D	1200V	40A	1.4V	TO247-3	
C4D60120D	1200V	60A	1.4V	TO247-3	
C4D10120H	1200V	10A	1.4V	TO247-2	
C4D15120H	1200V	15A	1.4V	TO247-2	

* 内陶瓷绝缘

GDsicsemi

SiC SBD - C

SiC Schottky diodes	Voltage	Current	VF	Packaging	
C4D20120H	1200V	20A	1.4V	TO247-2	
C4D30120H	1200V	30A	1.4V	TO247-2	
C4D40120H	1200V	40A	1.4V	TO247-2	
C4D50120H	1200V	50A	1.4V	TO247-2	
C4D60120H	1200V	60A	1.4V	TO247-2	
C3D10170H	1700V	10A	1.4V	TO247-2	
C5D10200H	2000V	10A	1.4V	TO247-2	
C5D20200H	2000V	20A	1.4V	TO247-2	
C5D20170H	1700V	20A	1.4V	TO247-2	
C3D25170H	1700V	25A	1.4V	TO247-2	
C3D50170H	1700V	50A	1.4V	TO247-2	

SiC MOSFET - A

GDsicsemi

SiC MOSFET	Vgs	Id	Rds(on)	Packaging
C2M1000065E	650V	4A	1000mΩ	TO252
C3M0380065F	650V	11A	380mΩ	TO252
C3M0380065N	650V	11A	380mΩ	TO220F
C3M0380065P	650V	11A	380mΩ	PDFN5*6
C3M0260065N	650V	14A	260mΩ	TO220F
C3M0260065E	650V	14A	260mΩ	TO220F
C3M0260065	650V	14A	260mΩ	PDFN5*6
C3M0180065M	650V	20A	380mΩ	TO252
C3M0180065F	650V	20A	380mΩ	TO220F
C3M0180065N	650V	20A	380mΩ	TO263-3
C3M0180065A	650V	20A	380mΩ	TO220
C3M0160065D	650V	23A	180mΩ	TO247-3
C3M0160065K	650V	23A	160mΩ	TO247-4
C3M0060065D	650V	39A	60mΩ	TO247-3
C3M0060065K	650V	39A	60mΩ	TO247-4
C3M0060065K	650V	39A	60mΩ	TOLL
C2M0040065K	650V	52A	40mΩ	TO247-4
C2M0040065D	650V	52A	40mΩ	TO247-3
C2M0020065K	650V	92A	20mΩ	TO247-4
C3M0015065K	650V	120A	15mΩ	TO247-4
C3M0015065D	650V	120A	15mΩ	TO247-3
C2M0010075D	750V	120A	10mΩ	TO247-3
C2M0010075K	750V	120A	10mΩ	TO247-4
C2M0010075T	750V	120A	10mΩ	TOLL
C3M0065090D	900V	36A	65mΩ	TO247-3

SiC MOSFET - B

GDsicsemi

Part Number	Vgs	Id	Rds(on)	Packaging
C2M0011090K	900V	175A	11mΩ	TO247-4
C3M0065100K	1000V	36A	65mΩ	TO247-4
C2M0160120D	1200V	19A	160mΩ	TO247-3
C2M0160120K	1200V	19A	160mΩ	TO247-4
C2M0080120D	1200V	36A	80mΩ	TO247-3
C2M0080120K	1200V	36A	80mΩ	TO247-3
C2M0040120D	1200V	60A	40mΩ	TO247-3
C2M0040120K	1200V	60A	40mΩ	TO247-4
C3M0016120DiSO	1200V	120A	16mΩ	TO247-3
C3M0016120D	1200V	120A	16mΩ	TO247-3
C3M0016120K	1200V	120A	16mΩ	TO247-4
C2M0016120DiSO	1200V	120A	16mΩ	TO247-3
C2M0016120D	1200V	120A	16mΩ	TO247-3
C2M0016120K	1200V	120A	16mΩ	TO247-4
C3M0016120KiSO	1200V	120A	16mΩ	TO247-4
C2M0013120DiSO	1200V	157A	13mΩ	TO247-3
C2M0013120D	1200V	157A	13mΩ	TO247-3
C2M0013120KiSO	1200V	165A	13mΩ	TO247-4
C2M0013120K	1200V	165A	13mΩ	TO247-4
C3M0021120K	1200V	81A	21mΩ	TO247-4
C3M0021120D	1200V	81A	21mΩ	TO247-3
C2M0025120D	1200V	80A	25mΩ	TO247-3
C2M0025120K	1200V	80A	25mΩ	TO247-4
C2M0025120DiSO	1200V	80A	25mΩ	TO247-3
C2M0025120KiSO	1200V	80A	25mΩ	TO247-4
C3M0032120K	1200V	63A	32mΩ	TO247-4
C3M0032120KiSO	1200V	63A	32mΩ	TO247-4
C3M0032120D	1200V	63A	32mΩ	TO247-3

SiC MOSFET - C

GDsicsemi

Part Number	Vgs	Id	Rds(on)	Packaging
C3M0032120DiSO	1200V	63A	32mΩ	TO247-3
C2M0035120D	1200V	55A	35mΩ	TO247-3
C3M0075120DiSO	1200V	32A	75mΩ	TO247-3
C3M0075120KiSO	1200V	32A	75mΩ	TO247-4
C3M0075120D	1200V	32A	75mΩ	TO247-3
C3M0075120K	1200V	32A	75mΩ	TO247-4
C3M0075120J	1200V	32A	75mΩ	TO263-7
GD3N150PF	1500V	3A	800mΩ	TO3PF-3
GD3N150DF	1500V	3A	800mΩ	TO252-3
GD4N150PF	1500V	4A	650mΩ	TO3PF-3
GD4N150DF	1500V	4A	650mΩ	TO252-3
GD9N150DF	1500V	9A	450mΩ	TO3PF-3
GD15N150PF	1500V	15A	160mΩ	TO3PF-3
C2M1000150D	1500V	3A	1000mΩ	TO247-3
C2M1200120L	1500V	2.5A	1200mΩ	TO268-2L
C2M1000170D	1700V	5A	1000mΩ	TO247-3
C2M1000170K	1700V	5A	1000mΩ	TO247-4
C2M1000170J	1700V	5A	1000mΩ	TO263-7
C2M0500170D	1700V	8A	500mΩ	TO247-3
C2M0040170D	1700V	67A	40mΩ	TO247-3
C2M0045170D	1700V	72A	45mΩ	TO247-3
C2M0045170DiSO	1700V	72A	45mΩ	TO247-3
C2M0045170P	1700V	72A	45mΩ	TO247-4
C2M0045170PiSO	1700V	72A	45mΩ	TO247-4
C2M0028170D	1700V	82A	28mΩ	TO247-3
C2M0028170P	1700V	82A	28mΩ	TO247-4
C2M0028170DiSO	1700V	82A	28mΩ	TO247-3
C2M0028170KiSO	1700V	82A	28mΩ	TO247-4
C2M5000330D	3300V	100MA	5000mΩ	TO247-3

SiC MOSFET - D

GDsicsemi

Part Number	Vgs	Id	Rds(on)	Packaging
C2M2000330D	3300V	1A	2000mΩ	TO3PF-3
C2M1000330D	3300V	8A	900mΩ	TO247-3
C2M1000330DiSO	3300V	8A	900mΩ	TO247-3
*C2M0050300K	3300V		50mΩ	TO247-4
*C2M0050330D	3300V		50mΩ	TO247-3
C2M0180650DiSOPLUS	6500V	20A	180mΩ	TO247-3PLUS

*: Suitable for AED

Contact US

TAIWAN Branch Office:

Tel: +886- 3- 563 7887
Fax:+886- 3- 563 7877
Mobile: +886- 956 800 088
Contact: Mr. Till Chang
E- Mail: till_chang@justlink-advtek.com

Hong Kong & SEA Branch Office

Tel: +852- 3691 9181
Fax: +852- 3691 9186
Mobile: +852- 9622 8808
Contact: Mr. Daniel Yan
E- Mail: danielyanck@gmail.com

Tel: 86-752-3320189
Fax: 86-752-3321989
Mobile: 13306312955
Email: chenquanhai@gdsicsemi.com

www.gdsicsemi.com

惠州市广大碳基半导体有限公司